Low-temperature transport, optical, magnetic and thermodynamic properties of Fe$_{1-x}$Co$_x$Si

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We report measurements of the electrical conductivity $\sigma(T)$, the optical reflectivity $R(\omega,T)$, the low-field ac magnetic susceptibility $\chi'(T,f)$, and the specific heat $C_p(T)$ for polycrystalline samples of Fe$_{1-x}$Co$_x$Si with $0 \leq x \leq 0.03$ at low temperatures. Between 130 and 300 K the temperature variation of $\sigma(\omega,T)$ is consistent with that of a hybridization-gap semiconductor and is very similar for all samples. Below 50 K $\sigma(0,T)$ strongly depends on the cobalt concentration $x$ and $d\sigma/dT$ decreases with decreasing $x$, changing sign from positive to negative in the range $0.01 \leq x \leq 0.02$. For $x \leq 0.0075$ the dc conductivity $\sigma$ tends to saturate below 0.1 K, indicating a semimetallic regime characterized by a very low density of itinerant carriers. For $x \geq 0.01$ the $\chi'(T)$ curves show maxima at different temperatures $T_\chi(x)$ manifesting a spin-glass-type freezing of magnetic moments below 1 K. The small values of $T_\chi(x)$ and the frequency dependences of $T_\chi$ both suggest a weak magnetic interaction. The low-temperature specific heat $C_p(T)$ contains a term $\gamma T$ that increases with increasing $x$ from 2.17 mJ mol$^{-1}$ K$^{-1}$ for pure FeSi to 7.67 mJ mol$^{-1}$ K$^{-1}$ for Fe$_{0.97}$Co$_{0.03}$Si. Together with the results of the optical measurements this implies a respectable low-temperature mass enhancement of the itinerant carriers on the order of 30.

I. INTRODUCTION

FeSi is a cubic narrow-gap semiconductor (space group $P2_13$) that has been claimed to share common features with a class of rare-earth compounds known as hybridization-gap semiconductors or Kondo insulators. The magnetic susceptibility $\chi(T)$ of FeSi shows a maximum at about 500 K and an activated behavior below that temperature corresponding to a narrow gap in the excitation spectrum. No magnetic order or spin-glass freezing occurs in this material, at least down to 0.04 K. At very low temperatures the electrical conductivity of FeSi is very low but metallic in character. Its isostructural counterpart CoSi is a diamagnetic semimetal with a temperature-independent susceptibility. The nature of the gap in the excitation spectrum of FeSi remains an open issue of debate from both the experimental and theoretical points of view. In fact, for some aspects of the results of $\sigma(T)$ and $\chi(T)$ measurements, difficulties in interpretation with theoretical calculations still exist. Furthermore, there is evidence for a possible difference between gaps in the charge and spin excitation channels, respectively.

Previous investigations have shown that the transport properties of FeSi are very much affected by replacing Fe by Co. With the aim to learn more about the ground state of FeSi we set out to study in more detail the question of possible consequences of Co doping on electronic and thermal properties, considering both itinerant and localized charge carriers. In addition, optical measurements were included to reveal details of the electronic excitation spectrum and a possible interplay between electronic and lattice excitations.

Below we report the results of this investigation of some low-temperature electrical-transport, optical, magnetic, and thermodynamic properties of pure and Co-doped FeSi. Fe$_{1-x}$Co$_x$Si forms disordered solid solutions with the B20 structure at all $x$. This system exhibits two critical concentrations $x_1 \approx 0.05$ and $x_2 \approx 0.8$ for the onset of an inhomogeneous long-period helimagnetic order, tentatively attributed to a Dzyaloshinsky–Moriya spin-orbit-type coupling, which can occur in the noncentrosymmetric B20 structure. The occurrence of a long-period helimagnetic order has previously been reported for the related B20 transition-metal compounds MnSi (Ref. 16) and FeGe (Ref. 17).

II. SAMPLES AND EXPERIMENTS

Polycrystalline ingots of Fe$_{1-x}$Co$_x$Si with Co concentrations in the range $0 \leq x \leq 0.03$ were prepared by melting together appropriate quantities of constituents in an rf furnace. Our samples, with dimensions of approximately $1.5 \times 1.5 \times 5$ mm, were cut from the ingots using spark erosion.

The electrical conductivity, the optical reflectivity, the ac magnetic susceptibility, and the specific heat were measured in varying ranges of temperature between 0.05 and 300 K. For each concentration of cobalt, all measurements reported below were done using the same sample. This matter is particularly important in the case of FeSi, the composition of which can vary from 49 to 50.5 at.% Si.

The electrical conductivity was measured by a standard low-frequency ac four-probe technique in the temperature range between 0.05 and 300 K. The samples were fixed to a heat sink with a thin layer of GE-7031 varnish at one end to
reduce the cooling-induced stress.3

The low-frequency and low-field ac magnetic susceptibility data were obtained with a conventional mutual-inductance technique in varying temperature ranges between 0.05 and 4 K. Measurements were made in the frequency range between 18 and 630 Hz and with an excitation-field amplitude in the range from 0.025 to 0.1 Oe. The signal of the pickup coil was measured with a two-channel lock-in amplifier monitoring simultaneously the in-phase \( x \) and the out-of-phase component \( \chi' \). A low-noise signal transformer was used to match the impedances of the pick-up coil and the lock-in amplifier.

The specific heat \( C_p(T) \) was measured using a relaxation-type method in the temperature range between 0.05 and 31 K. The temperatures in the range between 0.05 and 1 K were reached in a dilution refrigerator. Conventional \(^4\)He and \(^3\)He cryostats were used for temperatures between 0.35 and 4 K, and above 1.5 K, respectively.

The optical reflectivity \( R(\omega) \) of Fe\(_{1-x}\)Co\(_x\)Si has been measured for the samples with \( x = 0, 0.005, 0.02, \) and 0.03 in the frequency range between 15 and \( 10^5 \) cm\(^{-1} \), i.e., over almost four orders of magnitude in frequency and at selected fixed temperatures. The optical conductivity \( \sigma_{\chi}(\omega) \) was obtained by performing a Kramers-Kronig transformation of the reflectivity \( R(\omega) \) spectra extrapolated to lower and higher frequencies. Details concerning the experimental setup and the extrapolation procedure can be found in Ref. 19.

III. RESULTS, ANALYSIS, AND DISCUSSION

A. Electrical conductivity

The electrical conductivity \( \sigma(T) \) of polycrystalline samples of Fe\(_{1-x}\)Co\(_x\)Si was measured in the temperature range between 0.05 and 300 K for \( 0 \leq x \leq 0.01 \) and between 0.4 and 300 K for \( 0.02 \leq x \leq 0.03 \). The room-temperature conductivities \( \sigma_{300K} \) of the investigated materials fall into the range between \( 1.5 \times 10^3 \) and \( 4 \times 10^3 \) \( \Omega^{-1} \text{cm}^{-1} \). Our electrical-conductivity data are shown in Fig. 1 as a log-log plot of \( \sigma/\sigma_{300K} \) versus \( T \). Part of the same data for temperatures between 80 and 300 K are plotted as \( \ln(\sigma/\sigma_{300K}) \) versus \( T^{-1} \) and displayed in Fig. 2.

We first analyze the conductivity behavior for nominally pure FeSi. We note that although \( \sigma(T) \) was measured on a polycrystalline sample, the general features are very close to those revealed in experiments using single crystals. Below 300 K, there is a monotonic drop in conductivity by almost five orders of magnitude to the lowest measured temperature of 0.05 K. Between 200 and 300 K, the \( \ln(\sigma/\sigma_{300K}) \) versus \( T^{-1} \) curve tends to level off with increasing temperature, indicating that the material enters the electronically degenerate regime. In the whole temperature range measured we are not able to identify a regime of thermally activated conductivity

\[
\sigma \propto \exp \left( -\frac{E_{\text{gap}}}{2k_BT} \right)
\]  

(1)

over any extended range of temperature because the temperature variation of \( \sigma \) is, strictly speaking, characterized by a temperature dependent slope \( d\ln\sigma/d(T^{-1}) \).

It has previously been shown that above 100 K the behavior of \( \sigma \) of pure FeSi is consistent with that of a hybridization-gap semiconductor, i.e., a system with a strong renormalization of the noninteracting bands and their widths that leads to an enhanced electronic density of states (DOS) at the gap edges. While an applicability of a hybridization-gap-semiconductor approach to FeSi may be questioned on general grounds, it seems to consistently describe magnetic, thermodynamic, and transport properties of this material at temperatures exceeding 100 K. In addition, high-resolution angle-resolved photoemission studies of FeSi (Refs. 21 and 22) have shown the development of a band with spectacularly sharp features near the upper edge of the valence band, which strongly supports a picture involving two narrow bands at the edges of a narrow gap.
The assumptions that the electronic DOS can be approximated by two rectangular bands, each of width \( W \), separated by an energy gap \( E_g \) and that the mobility \( b \) of the itinerant charge carriers is limited by electron-phonon scattering; i.e., \( b \approx T^{-3/2} \), leads to

\[
\sigma \approx T^{-3/2} \left[ 1 - \frac{k_B T}{W} \ln \left( 1 + \exp \left( \frac{E_g + 2W}{2k_B T} \right) \right) \right] + \frac{k_B T}{W} \ln \left( 1 + \exp \left( \frac{E_g}{2k_B T} \right) \right),
\]

(2)

Here it is also assumed that the chemical potential \( \mu \) resides in the center of the energy gap and is temperature independent, which is consistent with electron-hole symmetry of the model DOS.\(^\text{10}\) These assumptions are expected to be valid at not too low temperatures, i.e., in the temperature range of the intrinsic regime. A fit of Eq. (2) to \( \sigma(T) \) of pure FeSi in the temperature range between 130 and 300 K, shown in Fig. 2 as the solid line through the data points of FeSi, yields \( E_g = 81 \text{ meV} \) and \( W = 39 \text{ meV} \), in fair agreement with analogous values reported in Refs. 20 and 10.

On the log-log scale used in Fig. 1 one recognizes a shoulder in the electrical conductivity data at \( T = 80 \text{ K} \). Below that temperature \( \sigma \) drops further with decreasing \( T \) but tends to saturate below 1 K, reaching \( 4.4 \times 10^{-2} \, \Omega^{-1} \text{ cm}^{-1} \) at 0.05 K. Nowhere in this regime is it possible to describe the data with a thermally activated behavior over any extended temperature range.

In previous studies of FeSi (Ref. 23) it has been claimed that in the limited range of temperatures between 2.5 and 40 K, \( \sigma(T) \) of pure FeSi can be described with a variable-range-hopping behaviour,\(^\text{24}\) i.e.,

\[
\sigma \approx \exp \left( - \left( \frac{T_{1/4}}{T} \right)^{1/4} \right).
\]

(3)

A fit of Eq. (3) to our \( \sigma(T) \) data of pure FeSi in the temperature range 2.5–20 K shown in Fig. 3 yields \( T_{1/4} = 1.43 \times 10^4 \text{ K} \), which is very close to the \( T_{1/4} \) value of 1.42 \times 10^4 \text{ K} reported in Ref. 23. For samples with \( x \neq 0 \), however, it may be seen that this type of approximation is not appropriate.

At the lowest temperatures below 0.18 K, the conductivity \( \sigma \) is well described by an expression of the form

\[
\sigma = \sigma_0 + m T^{\alpha},
\]

(4)

as shown in the inset of Fig. 1. In this regime we find \( \sigma_0 = 4.4 \times 10^{-2} \, \Omega^{-1} \text{ cm}^{-1} \), \( m = 0.72 \, \Omega^{-1} \text{ cm}^{-1} \text{ K}^{-3/2} \), and \( \alpha = 3.2 \). We note that the value of the exponent \( \alpha \) is very large compared with \( \alpha \approx 2 \) previously reported for metallic samples of doped semiconductors close to the metal to nonmetal transition.\(^\text{25}\)

We now focus on the \( \sigma(T) \) variation of Co-doped FeSi. Between 90 and 300 K, \( \sigma(T) \) of these samples is qualitatively similar to that of nominally pure material. Between 130 and 300 K the conductivity \( \sigma \) is again well described by Eq. (2) appropriate for a hybridization-gap semiconductor in the regime of intrinsic conductance (see Fig. 2). The energy gap \( E_g \) that follows from the analysis of our \( \sigma(T) \) data for Fe\(_{1-x}\)Co\(_x\)Si appears to be independent of the cobalt concentration \( x \) for materials with \( x \leq 0.02 \) and it slightly decreases with further increasing \( x \) (see Fig. 4).

Below 90 K \( \sigma(T) \) depends strongly on the doping level. In the \( \log_{10}(\sigma/\sigma_{300\text{ K}}) \) versus \( \log_{10}T \) plot shown in Fig. 1, the curves are seen to become less steep with increasing \( x \). Below about 30 K, \( \sigma/\sigma_{300\text{ K}} \) of Fe\(_{0.995}\)Co\(_{0.005}\)Si is noticeably higher than that of nominally pure FeSi, the difference amounting to 1/2 orders of magnitude at 1 K. Below 1 K, where \( \sigma \) of pure FeSi saturates, the conductivity of Fe\(_{0.995}\)Co\(_{0.005}\)Si keeps dropping steeply with decreasing \( T \) until it tends to saturate below 0.15 K, reaching a level, that is close to that of pure FeSi in this temperature range. The samples with \( x = 0.0075 \) and 0.01 show a \( \sigma(T) \) variation, which is qualitatively similar to that of Fe\(_{0.995}\)Co\(_{0.005}\)Si but their conductivities at \( T = 0.05 \text{ K} \) are higher than that of Fe\(_{0.995}\)Co\(_{0.005}\)Si by one and two orders of magnitude, respectively.

For Co-doped FeSi we were not able to identify regimes of thermally activated conductivity or of variable-range hop-
the metallic regime to zero and therefore a trend of $d$ with $s$. For this case, $dT$ clearly exhibits metallic behavior at low temperatures. However, we note that an expression of the form

$$d = \exp\left[-\left(\frac{T_{1/2}}{T}\right)^{1/2}\right]$$

appropriate for a regime of variable-range hopping in the presence of a Coulomb gap,\textsuperscript{26,27} i.e., when the single-particle density of states close to the chemical potential is depleted due to the Coulomb interaction between electrons, seems to describe our conductivity data for Fe$_{1-x}$Co$_x$Si with $0.005 < x < 0.01$ over substantial temperature ranges (see Fig. 5).

With increasing $x$ the conductivity saturation at very low temperatures that dominates the $\sigma(T)$ data of nominally pure FeSi becomes less pronounced and it is not well developed in the conductivity data of Fe$_{0.99}$Co$_{0.01}$Si. The saturation trend of $\sigma$ at low temperatures may be described qualitatively using an approach based on an evaluation of the derivative $d\ln\sigma/d\ln T$.\textsuperscript{28} This simple but instructive analysis is meant to allow for the identification of the type of conductivity from the $d\ln\sigma/d\ln T$ behavior at low temperatures. In the metallic regime $\sigma$ approaches nonzero values as $T$ tends to zero and therefore $d\ln\sigma/d\ln T$ is still nonzero at the lowest temperatures of 0.05 K reached in our experiments, the positive slope of the $d\ln\sigma/d\ln T$ versus log$_{10}T$ curves close to $T=0.05$ K suggests that all these samples are metallic as $T\to 0$. Below 0.08 K the electrical conductivity $\sigma(T)$ of Fe$_{1-x}$Co$_x$Si with $0.005 < x < 0.01$ can be well described by Eq. (4). The fitted values of the parameters $\sigma_0$ and $\alpha$ are plotted in Fig. 7 as functions of cobalt concentration $x$.

We have calculated the numerical derivative $d\ln\sigma/d\ln T$ using $\sigma(T)$ of our Fe$_{1-x}$Co$_x$Si samples. The results of this calculation are plotted versus $\ln T$ in Fig. 6. The peak between 100 and 200 K common to all samples reflects the crossover between the regimes of intrinsic and extrinsic conduction. According to this analysis of $d\ln\sigma/d\ln T$, pure FeSi clearly exhibits metallic behavior at low temperatures. For Fe$_{1-x}$Co$_x$Si with $0.005 < x < 0.01$, $d\ln\sigma/d\ln T$ first increases with decreasing temperature below 10 K and after reaching a maximum at a temperature, which depends on $x$, decreases with further decreasing $T$. Although for the samples with $0.005 < x < 0.01$, $d\ln\sigma/d\ln T$ is still nonzero at the lowest temperatures of 0.05 K reached in our experiments, the positive slope of the $d\ln\sigma/d\ln T$ versus log$_{10}T$ curves close to $T=0.05$ K suggests that all these samples are metallic as $T\to 0$. Below 0.08 K the electrical conductivity $\sigma(T)$ of Fe$_{1-x}$Co$_x$Si with $0.005 < x < 0.01$ can be well described by Eq. (4). The fitted values of the parameters $\sigma_0$ and $\alpha$ are plotted in Fig. 7 as functions of cobalt concentration $x$.

FIG. 5. $\ln(\sigma(500 K))$ vs $T^{-1/2}$ of Fe$_{1-x}$Co$_x$Si with $0 \leq x \leq 0.01$ between 0.05 and 300 K. Lines indicate fits of the $\sigma(T)$ data of the Co-doped materials using Eq. (5) in the temperature range between 0.2 and 4 K.

FIG. 6. $d\ln\sigma/d\ln T$ vs log$_{10}T$ of Fe$_{1-x}$Co$_x$Si.

FIG. 7. Zero-temperature conductivity $\sigma_0$ and the exponent $\alpha$ obtained from fitting Eq. (4) to the $\sigma(T)$ data of Fe$_{1-x}$Co$_x$Si plotted as functions of cobalt concentration $x$. The fitting ranges are 0.05–0.08 K and 0.35–0.5 K for $0 \leq x \leq 0.01$ and $0.02 \leq x \leq 0.03$, respectively. The lines are guides for the eye.
For Co concentrations \(x = 0.02\) and 0.03, the conductivity \(\sigma\) depends relatively weakly on temperature below 90 K (see Fig. 8). Here \(\sigma\) first decreases with decreasing \(T\), reaches a shallow minimum at approximately 50 K, and then increases with further decreasing temperature with a very small negative slope \(d\sigma/dT\). For both samples, the slope \(d\sigma/dT\) again changes sign at \(T \approx 1.5\) K and it remains down to the lowest measured temperature of 0.4 K. Well below 1 K, the electrical conductivity \(\sigma(T)\) is adequately fitted using Eq. (4) with \(a \approx 0.5\) and \(m \approx 60\) \(\Omega^{-1}\) \(\text{cm}^{-1}\) \(\text{K}^{-1/2}\) (see inset of Fig. 8). This implies that the temperature dependence of the conductivity \(\sigma(T)\) of \(\text{Fe}_{1-x}\text{Co}_x\text{Si}\) with \(x = 0.02\) and 0.03 close to \(T = 0\) is determined by the diffusion-channel term characteristic of disordered metals with low electron diffusivity. The diffusion-channel correction to the classical Boltzmann conductivity arises from quantum-interference effects when the scattering is predominantly elastic, and it is due to the Coulomb interaction between itinerant electrons whose combined total momentum \(p\) is small compared with the Fermi momentum \(p_F\).

We now comment on the composition dependence of the zero-temperature conductivity \(\sigma_0\) and the power-law exponent \(\alpha\) obtained using Eq. (4) and shown in Fig. 7. With decreasing \(x\) from 0.03 to 0.005, \(\sigma_0\) rapidly decreases by more than 4 orders of magnitude but it saturates below \(x = 0.005\). The saturation of the zero-temperature conductivity \(\sigma_0\) for \(x \approx 0.005\) suggests that an additional mechanism of conduction sets in at the level of \(\sigma_0 \approx 0.04\) \(\Omega^{-1}\) \(\text{cm}^{-1}\) and we will comment on this observation later. For 0.02 \(\leq x < 0.03\), i.e., well within the metallic regime, \(\alpha \approx 0.5\), independent of \(x\). With further decreasing \(x\) the exponent \(\alpha\) increases rapidly, reaching 3.5 at \(x = 0.075\) and varying only weakly with \(x\) for \(x \approx 0.075\). We note that positive and nonzero values of \(\sigma_0\) confirm our conclusion, based on the analysis of \(dln\sigma/dlnT\), that all our samples of \(\text{Fe}_{1-x}\text{Co}_x\text{Si}\) are metallic. Nevertheless, both the \(\sigma_0(x)\) and the \(\alpha(x)\) variation in the Co concentration range 0.005 \(\leq x \leq 0.03\) are indicative of the proximity of a metal-to-insulator transition.

The assumptions that the composition-driven metal-to-insulator transition is bound to occur in \(\text{Fe}_{1-x}\text{Co}_x\text{Si}\) with \(x = 0.005\) and that the partial replacement of Fe by Co leads to one itinerant electron per cobalt impurity implies a minimum metallic conductivity \(\sigma_{\text{min}}\) given by

\[
\sigma_{\text{min}} = C_3 \frac{e^2}{\hbar l_{\text{min}}} \approx 37 - 74 \ \Omega^{-1}\ \text{cm}^{-1}.
\]

Here \(l_{\text{min}}\) is the shortest possible mean free path for which we take the mean separation between impurities, and \(C_3\) lies in the range between 0.025 and 0.05. For \(\text{Fe}_{1-x}\text{Co}_x\text{Si}\) with \(x = 0.005\) we calculate \(l_{\text{min}} \approx 17\) Å. In Fig. 9 we plot the power-law exponent \(\alpha\) as a function of \(\sigma_0/\sigma_{\text{min}}\). We note that \(\alpha \approx 0.5\) for \(\sigma_0/\sigma_{\text{min}} > 1\) and \(\alpha \approx 3.5\) when \(\sigma_0/\sigma_{\text{min}}\) is much less than unity (3 orders of magnitude). Apart from the somewhat large values of \(\alpha\) at the lowest impurity concentrations \(x\), the \(\alpha(\sigma_0/\sigma_{\text{min}})\) variation is in general agreement with what is usually observed on the metallic side of the metal to nonmetal transition of doped semiconductors.

We note, however, that a transition to a nonmetallic state implies that \(\sigma_0\) ought to decrease further with decreasing \(x\) below 0.005 and should vanish at a Co concentration \(x\) somewhat below 0.005, in obvious disagreement with our experimental results (see Fig. 7). A possible scenario that is consistent with our electrical conductivity \(\sigma(T)\) data of \(\text{Fe}_{1-x}\text{Co}_x\text{Si}\) is that below 0.1 K, FeSi enters a semimetallic regime characterized by a very low density of itinerant carriers as implied by the magnitude of \(\sigma_0^2\). This interpretation gains further support from a comparison of the temperature dependences of the conductivity in pure and moderately doped FeSi. While the values of the zero-temperature conductivity \(\sigma_0\) of nominally pure FeSi and \(\text{Fe}_{0.995}\text{Co}_{0.005}\text{Si}\) are almost equal, \(\sigma(T)\) of these two materials varies in dramatically different ways at intermediate temperatures as shown in Fig. 1. Additionally, for pure FeSi the results of the ac conductivity measurements in the frequency range between 20 Hz and 1 GHz (Ref. 4) are consistent with an increase of the dielectric constant by an order of magnitude with decreasing temperature from 4 to 0.08 K, again suggestive of a metallic state. A further discussion on the density and mobility of
charge carriers in FeSi at low temperatures will be presented in a forthcoming publication.\textsuperscript{32}

Taken together, the \( \sigma(T) \) behavior of nominally pure and Co-doped FeSi is consistent with that of impure hybridization-gap semiconductors, for which in the intrinsic regime at high temperatures, the \( \sigma(T) \) curves are expected to depend only slightly on doping. On the other hand, a strong concentration dependence of \( \sigma(T) \) is expected in the regime of extrinsic conductance at low temperatures. The energy gap \( E_{\text{gap}} = 81 \) meV that follows from our \( \sigma(T) \) data for nominally pure FeSi between 130 and 300 K is in fair agreement with our optical-conductivity results presented in Sec. III B and in Refs. 19 and 32, and also with the results of other experiments probing the width of the gap in the electronic excitation spectrum.\textsuperscript{10,33–36}

Finally, we note that in the Fe\( _{1-x} \)Co\( _x \)Si alloy series the transition from the regime of conductance characterized by a positive sign of \( d\sigma/dT \) to the regime in which \( d\sigma/dT \) is negative, occurring at Co concentrations \( x \) in the range between 0.01 and 0.02 at \%, becomes manifest at temperatures just below the regime of intrinsic conductance. This is quite in contrast, for example, to antimony-doped germanium, for which an intermediate activation regime characterized by an activation energy \( E_1 \), has clearly been identified.\textsuperscript{37}

\section*{B. Optical conductivity}

Figure 10 presents \( \sigma_1(\omega) \) at several selected temperatures for Fe\( _{1-x} \)Co\( _x \)Si with \( x = 0, 0.005, 0.02, \) and 0.03. We immediately note the overall equivalence, at least qualitatively, among the optical properties of the various alloys with different composition. As observed previously for FeSi\textsuperscript{19,33} we note the same progressive opening of a gap with decreasing temperature, leading to the suppression of spectral weight in the far- and mid-infrared range (FIR-MIR). The dc limit of \( \sigma_1(\omega) \) at each temperature is consistent with the measured dc conductivity (see Sec. III A). For \( x = 0.02 \) and 0.03 we do observe a residual metallic contribution to \( \sigma_1(\omega) \) at low temperatures, which manifests itself by a constant \( \sigma_1(\omega \to 0) \neq 0 \) behavior below the FIR spectral range. This is distinctly different from the behavior of \( \sigma_1(\omega) \) for \( x = 0 \) and 0.005, where the metallic component cannot be resolved at low temperatures. We also note that the lost spectral weight due to the opening of the gap piles up at the gap absorption. Particularly for \( x = 0, 0.005, \) and 0.02, \( \sigma_1(\omega) \) at low temperatures displays peaks at \( E_{\text{gap}} \) exceeding the signal of the 300 K curve.\textsuperscript{19,32}

However, for \( x = 0.03 \) the gap feature is barely recognized and the transferred spectral weight does not induce a sizable peak in \( \sigma_1(\omega) \). This is mainly the consequence of the higher reflectivity of the \( x = 0.03 \) alloy in the FIR-MIR range. Nevertheless, the total spectral weight is fully recovered by \( \omega < 4 \omega_{\text{gap}} \) in all investigated alloys. Since no softening of the sharp phonon modes below the gap energy is observed, we conclude that the doping neither changes the electron-lattice coupling nor affects the symmetry of the crystal lattice, in agreement with previous x-ray and neutron scattering results.\textsuperscript{11,13,14} In addition, their relative spectral weight or intensity remains unchanged.

The rather conventional and phenomenological approach, based on the classical Lorentz-Drude dispersion theory,\textsuperscript{38} allo-

\begin{figure}
\centering
\includegraphics[width=\textwidth]{fig10}
\caption{Optical conductivity \( \sigma_1(\omega) \) of Fe\( _{1-x} \)Co\( _x \)Si with \( x = 0, 0.005, 0.02, \) and 0.03 at fixed temperatures in the range between 10 and 300 K.}
\end{figure}
term, one may estimate the effective mass \( m^* \) and the concentration \( n \) of the itinerant charge carriers. This may be achieved by comparing the corresponding plasma frequency \( \omega_p \) inferred from the fits, with the Sommerfeld \( \gamma(T \to 0) \) value of the electronic contribution to the specific heat. With \( \omega_p = 1832 \) and \( 2652 \, \text{cm}^{-1} \) and \( \gamma = 5.7 \) and \( 7.6 \, \text{mJ} \, \text{mol}^{-1} \, \text{K}^{-2} \) (see Sec. III D) we obtain \( m^*/m_e \sim 30 \), with \( n = 1.0 \times 10^{21} \) and \( 2.1 \times 10^{21} \, \text{cm}^{-3} \) for \( x=0.02 \) and 0.03, respectively. The latter numbers are consistent with additional charge carriers of the order of 1 electron per cobalt atom. For \( x=0 \) and 0.005, the disappearance of the Drude component below 40 K prohibits this procedure. However, a simple linear extrapolation of \( \omega_p \) for alloys with \( x<0.02 \) and taking into account the corresponding \( y \) results again in a mass enhancement \( m^*/m_e \) of the order of 30. In this connection we note that cyclotron masses as high as 14.5\( m_e \) have been deduced from the results of a study of the de Haas–van Alphen effect of MnSi, a weak itinerant ferromagnet with the B20 structure. 39

C. Magnetic susceptibility

In Fig. 11 we show the real part \( \chi'(T) \) of the complex ac magnetic susceptibility for the samples with \( x=0.01, 0.02, \) and 0.03 between 0.05 and 4 K. In the same temperature range, the \( \chi'(T) \) curve of nominally pure FeSi follows a Curie-Weiss-type law with a paramagnetic Curie temperature \( \Theta = -0.036 \, \text{K} \) and a very low value of the Curie constant. Well defined maxima in the \( \chi' \) versus \( T \) plots appear at \( T_f = 0.09, 0.40, \) and 0.67 K for the alloys containing 1, 2, and 3 at % of cobalt, respectively, suggestive of a spin-glass-type freezing of magnetic moments. Since the appearance of the \( \chi'(T) \) maxima occur at temperatures that increase with increasing \( x \), this moment-freezing phenomenon is most likely related with the Co substitutions.

Above the respective temperatures \( T_f \), the \( \chi' \) versus \( T \) variations can be well fitted using a Curie-Weiss-type law. The value of the effective moment per cobalt atom increases with increasing Co concentration. For the samples with \( x=0.02 \) and 0.03, \( \Theta \) is positive and of the order of \( T_f \), indicating predominantly ferromagnetic interactions. On the contrary, for \( \text{Fe}_{0.99}\text{Co}_{0.01}\text{Si} \), \( \Theta \) is negative and of a much smaller absolute value than the corresponding \( T_f \), indicating a trend towards weak antiferromagnetic coupling between magnetic moments. This sign change of the interaction may be related with a decrease of the characteristic length \( k_F^{-1} \) of the RKKY-type interaction with increasing carrier concentration. Here \( k_F \) is the Fermi wave vector, which, as our electrical conductivity results shown before in Sec. III A indicate, is expected to continuously increase with Co doping on the level of a few at %.

In Fig. 12 we plot the temperatures \( T_f \) at which the maxima in \( \chi'(T) \) occur, as a function of cobalt concentration \( x \). For comparison, in the inset of Fig. 12, we show the Curie temperatures \( T_C \) of \( \text{Fe}_{1-x}\text{Co}_x\text{Si} \) with \( x \approx 0.05 \) taken from Ref. 14. The plots \( T_f(x) \) and \( T_C(x) \) imply that both the moment freezing and the onset of long-range magnetic order require that critical concentrations of Co doping are exceeded. The occurrence of a critical concentration of magnetic impurities for magnetic-moment freezing is characteristic of insulating spin glasses with short-range magnetic interaction. 40 On the other hand this is somewhat unusual for metallic spin glasses with long-range RKKY-type interaction. While our electrical conductivity \( \sigma(T) \) results indicate that \( \text{Fe}_{1-x}\text{Co}_x\text{Si} \) samples with \( x \approx 0.01 \) are metallic (see Sec. III A), the density of itinerant carriers may be insufficient to effectively mediate the magnetic interaction between the Co moments. We note surprisingly small values of \( T_f/x \), which fall in the range between 9 and 22 K. Typical metallic spin glasses are characterized by much higher values of \( T_f/x \), e.g., \( T_f/x \approx 10^3 \, \text{K} \) for \( \text{Au}_{1-x}\text{Fe}_x \). 40 Values of \( T_f/x \) that are of similar magnitude to our results for \( \text{Fe}_{1-x}\text{Co}_x\text{Si} \) have previously been reported for the spin-glass systems \( \text{La}_{1-x}\text{Gd}_x\text{Al}_2 \), \( \text{Y}_{1-x}\text{Gd}_x\text{Al}_2 \), and \( \text{La}_{1-x}\text{Gd}_x\text{B}_6 \), all with a weak exchange interaction between Gd moments, mediated by itinerant electrons. 31

We have also measured \( \chi'(T) \) curves near \( T_f \) for several excitation frequencies \( f \) in the range between 18 and 630 Hz. The \( \chi' \) versus \( T \) maxima shift to higher temperatures with increasing frequency. Fitting the \( T_f(f) \) data with a Vogel-Fulcher-type relation
The fitting parameters $g_0 < \text{excess specific heat} C_p$ centered at approximately 8.5 K, indicating a large
with our evaluation of the very small values of $T_j$, values, indicating
that the relaxation behavior is close to Arrhenius type. Arrhenius-type relaxations are characteristic of metallic spin
glasses with a strongly reduced RKKY interaction and of insulating spin glasses with low concentrations of magnetic
moments. The observed type of relaxation is compatible with our evaluation of the very small values of $T_j$.

D. Specific heat

The complete set of the $C_p(T)$ data for all our samples of Fe$_{1-x}$Co$_x$Si, with the exception of Fe$_{0.9925}$Co$_{0.0075}$Si, in the
temperature range between 0.06 and 30 K, is shown in Fig.
13. The same data, in the form of $C_p/T$ versus $T^2$, are plotted in Fig. 14.

First we note a broad maximum in $C_p/T$ of nominally
pure FeSi centered at approximately 8.5 K, indicating a large
excess specific heat $C_{ex}(T)$. The FeSi results between 1.5
and 30 K are very well fitted by the sum of contributions of the usual low-temperature electronic and lattice excitations and a Schottky anomaly resulting from excitations within a
two-level system with a single interlevel energy $\Delta$, i.e.,

$$ C_p = \gamma T + \beta T^3 + \delta T^5 + A \left( \frac{\Delta}{k_B T} \right)^2 $$

$$ \times \left[ 1 + \exp \left( \frac{\Delta}{k_B T} \right) \right]^{-2} \exp \left( \frac{\Delta}{k_B T} \right). $$  

This fit is shown as a solid line through the data points of
FeSi in Fig. 14. The Schottky anomaly is characterized by a
level separation $\Delta \approx 2$ meV and an entropy release of
0.029 $R$ at 30 K. This Schottky anomaly is distinctly smaller for the sample with $x = 0.005$ and it cannot be identified in the $C_p(T)$ data for the samples with $x \geq 0.01$ (see Fig. 14).

The fitting parameters $\gamma$, $\beta$, and $\delta$ for the two samples with
$0 \leq x \leq 0.005$ are given in Table I.

![Image](image1.png)

**FIG. 13.** Specific heat $C_p$ of Fe$_{1-x}$Co$_x$Si as a function of temperature between 0.06 and 30 K plotted on log-log scales.

![Image](image2.png)

**FIG. 14.** $C_p/T$ vs $T^2$ of Fe$_{1-x}$Co$_x$Si. The solid and dashed lines indicate the fits of Eqs. (8) and (11) to the $C_p$ data for the samples with $x = 0.005$ and $x = 0.01$, respectively (see text). The dashed-dotted line indicates the Debye contribution of acoustic lattice excitations. Inset shows the difference $\gamma - \gamma_0$ between the coefficients of the linear terms to $C_p(T)$ of the cobalt-doped and pure FeSi, plotted as $(\gamma - \gamma_0)/x$ vs $x$.

In Fig. 14, we also show the expected acoustic phonon contribution for FeSi, which we have calculated from the results of low-temperature measurements of the elastic moduli $c_{11}$, $c_{44}$ and $\delta(c_{11} - c_{12})$ (Ref. 34) using the Born–von Kármán formula for the average sound velocity $v_s$ (Ref. 43)

$$ \frac{3}{v_s^2} = \rho \left[ \frac{2}{c_{44}^2} + \frac{1}{c_{11}^2} + \frac{3}{c_{12}} \right] \left[ \frac{1}{c_{44}^2} - \frac{1}{c_{11}^2} \right]. $$

Here $\rho$ is the mass density. Equation (9) is valid for nearly isotropic cubic crystals, i.e., when the anisotropy parameter

$$ \eta = \frac{c_{12} - c_{11} + 2c_{44}}{c_{11} - c_{44}} $$

is small compared with unity. For FeSi $\eta = 0.21$, which indicates a fairly low elastic anisotropy of this material.

The "elastic" Debye temperature $\Theta_D = 341$ K that follows from the average sound velocity $v_s$ obtained in the way described above is in good agreement with the "thermodynamic" Debye temperatures $\Theta_D$ of 369 and 357 K, which are compatible with the fitted values of the parameter $\beta$ for our materials with $x = 0$ and 0.005, respectively. In this connection we note that for various crystalline solids, including such different materials as elemental metals and ionic salts,
TABLE II. Parameters of the fits of Eq. (11) to the specific heat $C_p(T)$ data of Fe$_{1-x}$Co$_x$Si with 0.01 $\leq x \leq$ 0.03 (see text).

<table>
<thead>
<tr>
<th>$x$</th>
<th>$\gamma$ (mJ mol$^{-1}$ K$^{-2}$)</th>
<th>$B_1$ (J mol$^{-1}$ K)</th>
</tr>
</thead>
<tbody>
<tr>
<td>0.01</td>
<td>4.5</td>
<td>0.07</td>
</tr>
<tr>
<td>0.02</td>
<td>5.7</td>
<td>0.20</td>
</tr>
<tr>
<td>0.03</td>
<td>7.6</td>
<td>0.24</td>
</tr>
</tbody>
</table>

the Debye temperatures $\Theta_D^x$ and $\Theta_D^s$ often differ by a few percent even if the latter is determined from low-temperature elastic-moduli data.\textsuperscript{43–45}

For analyzing the $C_p(T)$ data of Fe$_{1-x}$Co$_x$Si with 0.01 $\leq x \leq$ 0.03 at temperatures above 5 K, we recall that our $\chi'(T)$ results (Sec. III C) indicate these samples to exhibit a spin-glass-type freezing of magnetic moments below 1 K. Therefore, we assume that the main contributions to $C_p$ are from electronic, lattice, and high-temperature spin-glass excitations, i.e.,

$$C_p = \gamma T + \beta T^3 + \delta T^5 + BT^{-2}. \, \, \, (11)$$

The fits of the $C_p(T)$ data using Eq. (11) are shown as the dashed lines in Fig. 14. For materials with $x \geq 0.01$ a precise evaluation of the cubic term $\beta T^3$ meets difficulties because of the large magnetic contribution to the specific heat. The linear term $\gamma T$, however, can reliably be determined as it appears to be rather insensitive to the details of the fitting procedure. The fitted values of $\gamma$ and $B$ for Fe$_{1-x}$Co$_x$Si with 0.01 $\leq x \leq$ 0.03 are given in Table II.

For Fe$_{1-x}$Co$_x$Si, the coefficient $\gamma$ of the linear term to the specific heat above 5 K increases with increasing doping level $x$ (see Tables I and II). Interpreting the linear term $\gamma T$ of nominally pure FeSi as being due to an electronic density of states at the Fermi energy, we arrive at a surprisingly large electronic specific-heat-heat parameter when considering the low concentration of itinerant carriers, as implied by our electrical conductivity $\sigma(T)$ results described in Sec. III A. For cobalt-doped materials, the assumption that the difference $(\gamma - \gamma_0)T$ between the linear terms to $C_p(T)$ of doped and pure FeSi corresponds to one itinerant electron per cobalt impurity, leads to an average value of $(\gamma - \gamma_0)/x$ of 0.2 J mol$^{-1}$ K$^{-2}$, suggestive of a considerable enhancement of the effective mass (see inset of Fig. 14). This implies that at low temperatures the Fermi level resides in a partially filled narrow band—a rather unusual scenario for a 3$d$ transition-metal system.

For Fe$_{1-x}$Co$_x$Si with $x \geq 0.02$, the magnetic contribution $C_m(T)$ to the total measured specific heat $C_p(T)$, obtained by subtracting off the estimates of the electronic and the lattice terms, exhibits broad maxima at temperatures that are distinctly higher than the respective freezing temperatures $T_f$. This observation is consistent with our conjecture of a spin-glass-type freezing of magnetic moments in these materials because in spin glasses a substantial difference between $T_f$ and the temperature of the maximum in $C_p(T)$ has often been observed.\textsuperscript{40} The magnetic entropy $\Delta S_m$, obtained from the magnetic specific heat $C_m$ via

$$\Delta S_m = \int_{T_f}^{T} \frac{C_m}{T} dT', \, \, \, (12)$$

saturates at 30 K reaching $\approx 0.20 R$ per mole of Co (see Fig. 15). The magnetic entropy released below $T_f$ removes only about 18 and 25% of the saturation value of $\Delta S_m$ for materials with $x = 0.02$ and 0.03, respectively. This implies a considerable short-range order above $T_f$, which is a common feature of spin glasses.\textsuperscript{40}

**IV. CONCLUSIONS**

The electrical conductivity, the optical reflectivity, the ac magnetic susceptibility, and the specific heat of Fe$_{1-x}$Co$_x$Si with 0 $\leq x \leq$ 0.03 have been measured in varying temperature ranges between 0.05 K and 300 K. Our electrical conductivity data imply that FeSi is an impure hybridization-gap semiconductor ($E_g \approx$ 80 meV) at moderate temperatures but enters a semimetallic state with a very small number of itinerant carriers below 0.1 K. The $T^{1/2}$ variation of the electrical conductivity $\sigma$ of Fe$_{1-x}$Co$_x$Si with $x = 0.02$ and 0.03 below 0.5 K indicates that the temperature dependence of $\sigma$ of these materials close to $T = 0$ is dominated by the diffusion-channel term arising from Coulomb interaction among itinerant electrons. The optical data confirm both the magnitude of the gap and the trend to its slight reduction for the alloy with 3 at% Co content.

For Fe$_{1-x}$Co$_x$Si with $x \geq 0.02$, a spin-glass-type freezing of magnetic moments is observed between 0.09 and 0.7 K. The small values of $T_f/x$ and the $T_f(f)$ variations are both indicative of a weak interaction among the moments. Upon reducing the cobalt concentration $x$, this interaction changes from ferromagnetic to antiferromagnetic in the range 0.01 $\leq x \leq$ 0.02. This crossover is accompanied by a decrease of $T_f/x$ by a factor of 2 leading to a concave down variation of $T_f$ versus $x$.

The specific heat $C_p(T)$ of Fe$_{1-x}$Co$_x$Si contains a term $\gamma T$ that increases with increasing $x$ from 2.17 mJ mol$^{-1}$
K for FeSi to 7.6T mJ mol K for Fe0.9Co0.1Si. Assuming that the difference (γ − γ0)T between the linear terms of C(T) of doped and pure FeSi is due to an additional electronic DOS at the Fermi energy and that this DOS corresponds to one itinerant electron per cobalt impurity, leads to values of (γ − γ0)/x reaching 0.24 J mol K .2, indicating a considerable enhancement of the effective mass. The numerical estimate of the mass enhancement using optical and specific-heat data, as explained in Sec. III B, gives m*/m−30, a surprisingly high value for 3d transition-metal alloys. Thus the low-temperature state of FeSi is that of a strongly correlated metal with a very low concentration of itinerant charge carriers, again a rather unusual feature for a 3d transition-metal compound.

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